200V 9.1mΩ N-Ch Power MOSFET

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

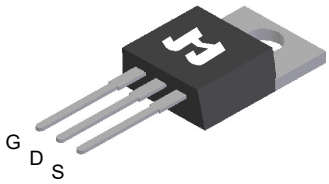
Product Summary

Parameter	Value	Unit
V_{DS}	200	V
$V_{GS(th)\_Typ}$	3.3	V
I_D (@ V_{GS} = 10V) (1)	129	A
$R_{DS(ON)\_Typ}$ (@ V_{GS} = 10V)	9.1	mΩ

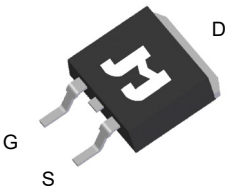
Applications

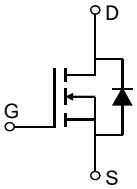
- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

TO-220-3L Top View



TO-263-3L Top View



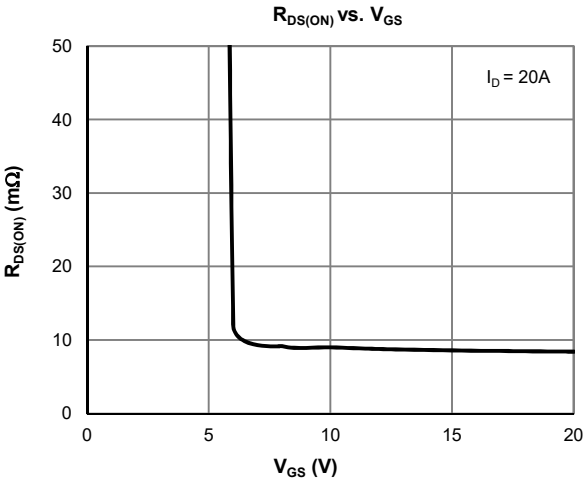


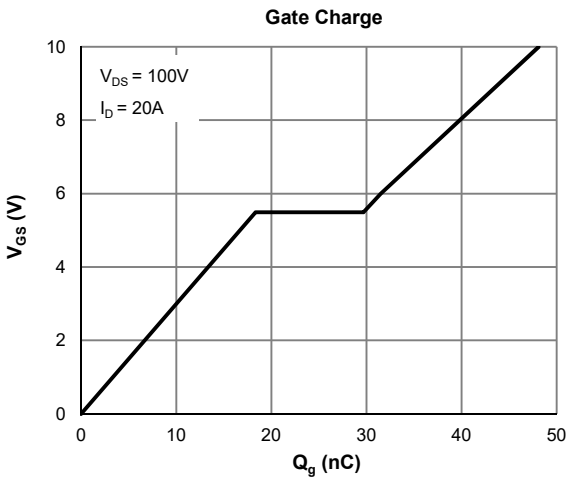
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH2010BC-U	TO-220-3L	3	SH2010B	NA	-55 to 175	Tube	50
JMSH2010BE-13	TO-263-3L	3	SH2010B	1	-55 to 175	13-inch Reel	800

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	200	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (1)	T_C = 25°C	I_D	129	A
	T_C = 100°C		91	
Pulsed Drain Current (2)		I_{DM}	517	A
Avalanche Current (3)		I_{AS}	41	A
Avalanche Energy (3)		E_{AS}	841	mJ
Power Dissipation (4)	T_C = 25°C	P_D	500	W
	T_C = 100°C		250	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C





Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
STATIC PARAMETERS							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V		200			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 160V, V_{GS} = 0V				1.0	μA
			T_J = 55°C			5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V				±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA		2.5	3.3	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A	TO-263-3L		9.1	10.7	mΩ
			TO-220-3L		9.4	10.9	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 20A			55		S
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V			0.67	1.0	V
Diode Continuous Current	I_S	T_C = 25°C				129	A
DYNAMIC PARAMETERS (6)							
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 100V, f = 1MHz			3318		pF
Output Capacitance	C_{oss}				436		pF
Reverse Transfer Capacitance	C_{rss}				41		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz			3.4		Ω
SWITCHING PARAMETERS (6)							
Total Gate Charge (@ V_{GS} = 10V)	Q_g	V_{GS} = 0 to 10V V_{DS} = 100V, I_D = 20A			48		nC
Total Gate Charge (@ V_{GS} = 6.0V)	Q_g				32		nC
Gate Source Charge	Q_{gs}				18.3		nC
Gate Drain Charge	Q_{gd}				11.3		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = 10V, V_{DS} = 100V R_L = 5.0Ω, R_{GEN} = 6Ω			18.3		Quantity (pcs
Turn-On Rise Time	t_r				27		ns
Turn-Off DelayTime	$t_{D(off)}$				38		800
Turn-Off Fall Time	t_f				19.4		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 15A, dI_F/dt = 100A/μs			130		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 15A, dI_F/dt = 100A/μs			667		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	60	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.30	0.36	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 175°C.
3. This single-pulse measurement was taken under the following condition [L = 1mH, V_{GS} = 10V, V_{DD} = 100V] while its value is limited by T_{J_Max} = 175°C.
4. The power dissipation P_D is based on T_{J_Max} = 175°C.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

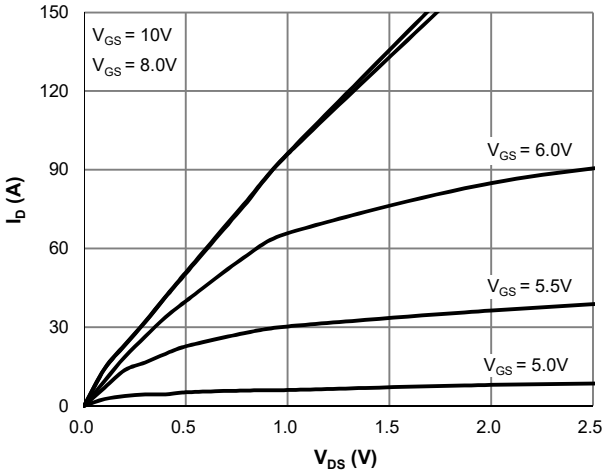


Figure 1: Saturation Characteristics

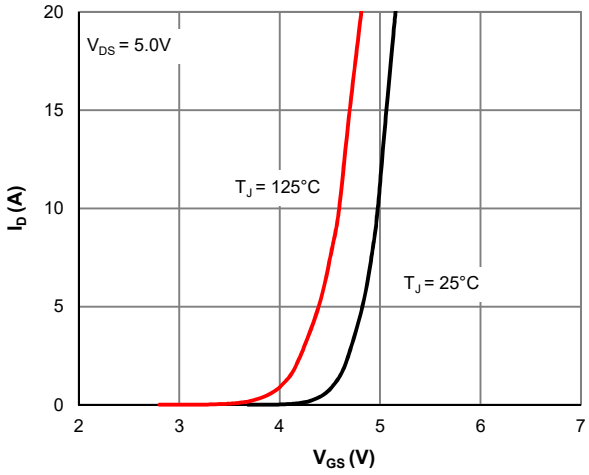


Figure 2: Transfer Characteristics

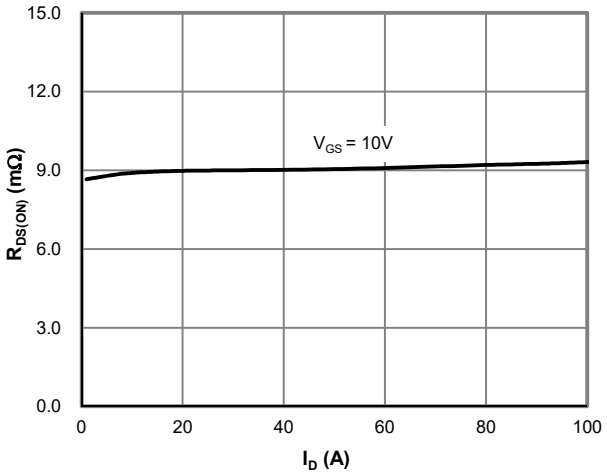


Figure 3: $R_{DS(ON)}$ vs. Drain Current

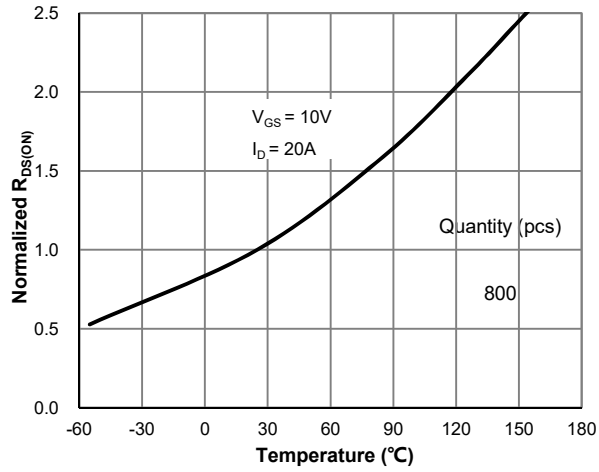


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

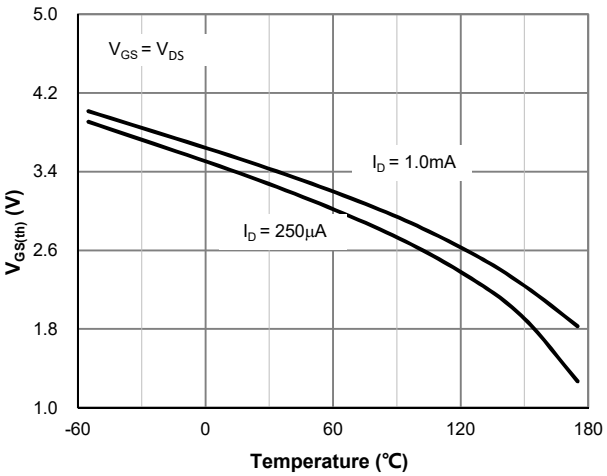


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

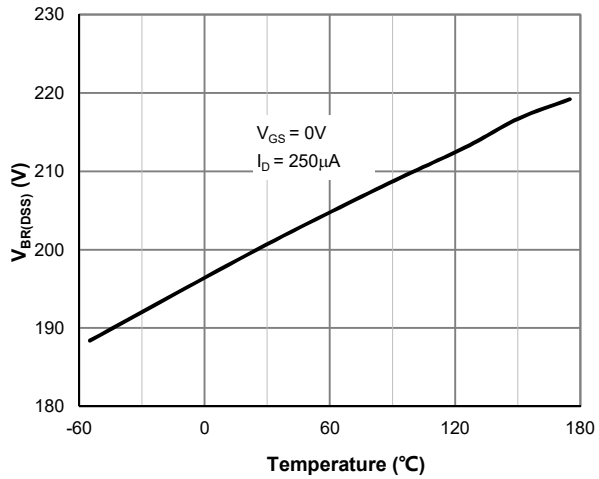


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

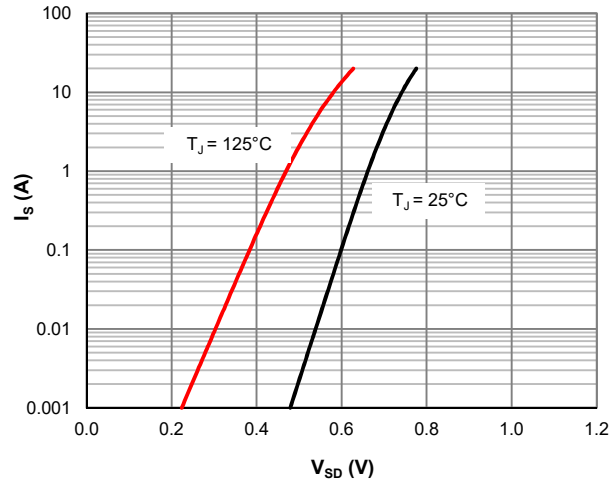


Figure 7: Body-Diode Characteristics

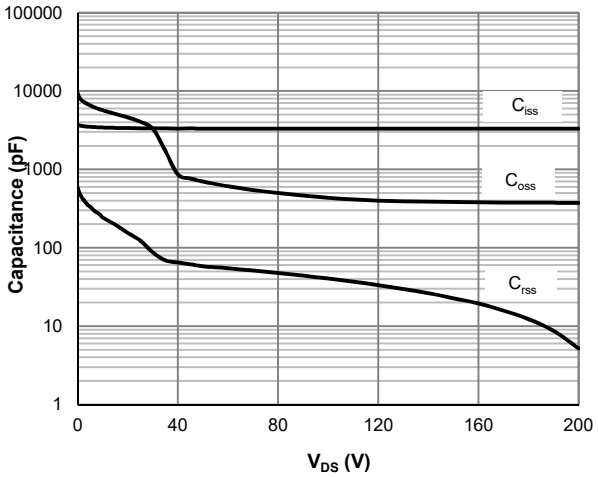


Figure 8: Capacitance Characteristics

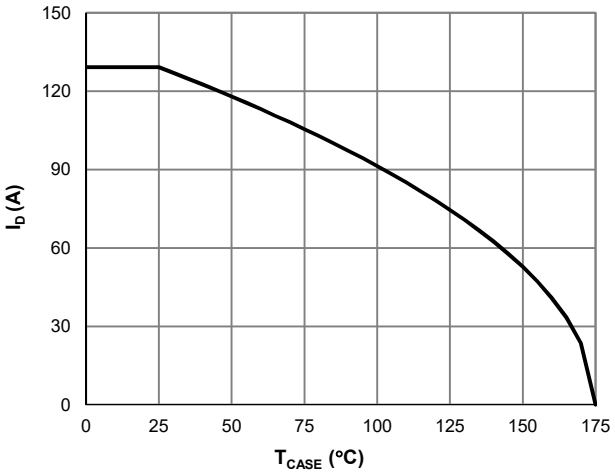


Figure 9: Current De-rating

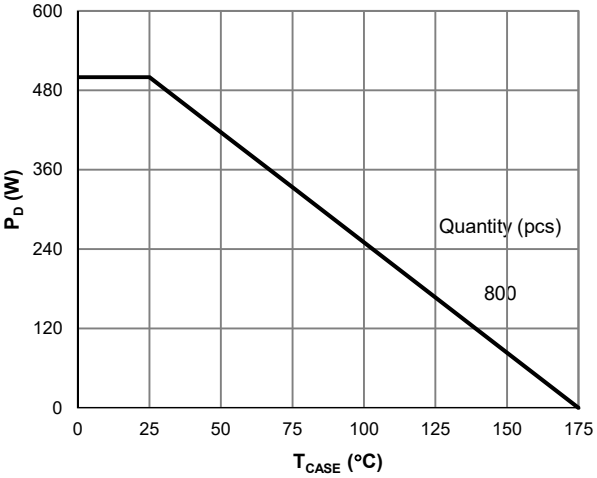


Figure 10: Power De-rating

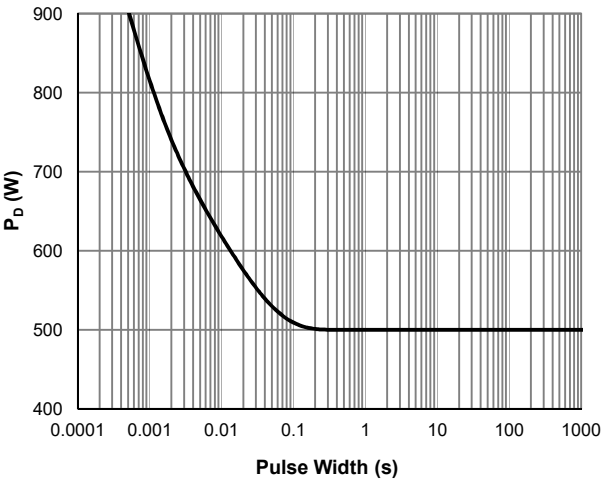


Figure 11: Single Pulse Power Rating, Junction-to-Case

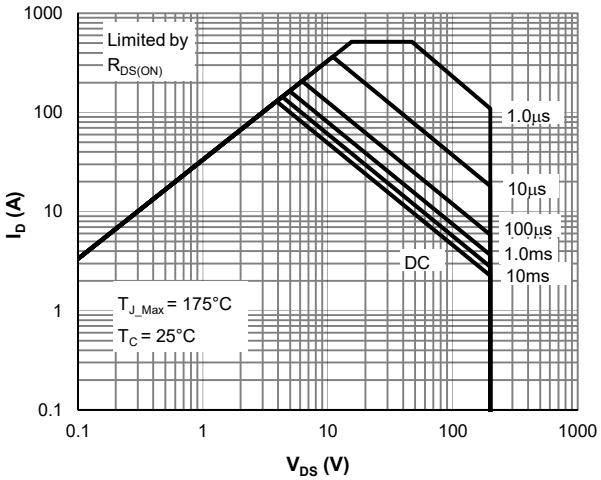


Figure 12: Maximum Safe Operating Area

Typical Electrical & Thermal Characteristics

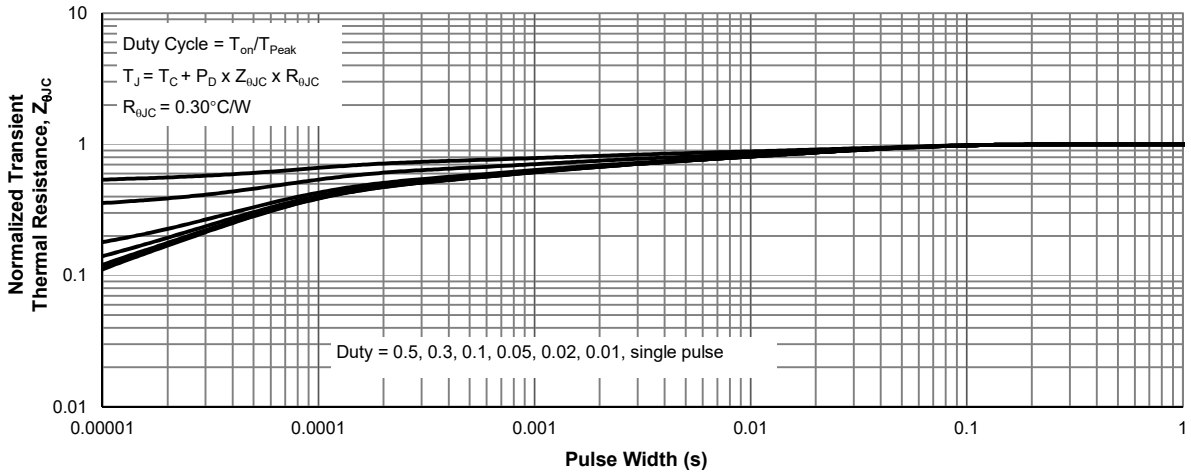
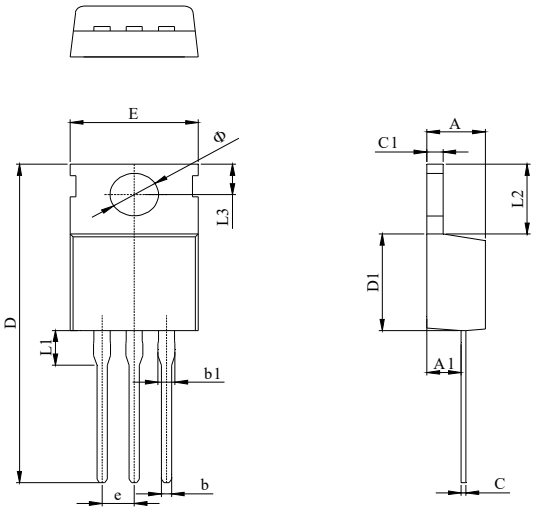


Figure 13: Normalized Maximum Transient Thermal Impedance

Quantity (pcs)
800

TO-220-3L Package Information

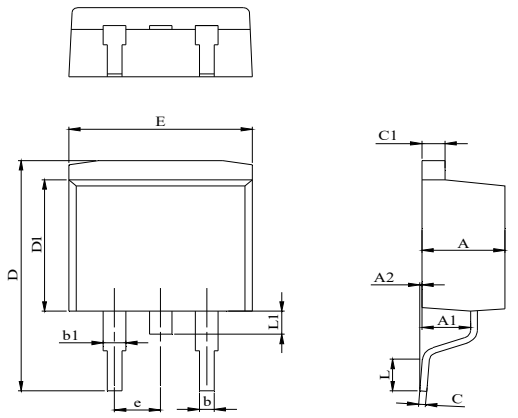
Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.70
A1	2.20		3.00
b	0.70		0.95
b1	1.14		1.70
C	0.40		0.60
C1	1.15		1.40
D	28.00		29.80
D1	8.80		9.90
E	9.70		10.50
L1			3.80
L2	6.25		6.90
L3	2.40		3.00
e		2.54 BSC	
Φ	3.58		3.85

TO-263-3L Package Information

Package Outline

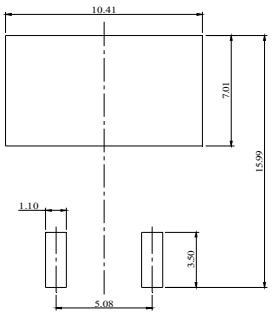


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.77
A1	2.30		2.89
A2	0.00	0.10	0.25
b	0.70		0.96
b1	1.17		1.70
C	0.30		0.60
C1	1.15		1.42
D	14.10		15.88
D1	8.50		9.60
E	9.78		10.36
L	1.78		2.79
L1			1.75
e		2.54	

Quantity (pcs

800

Recommend Soldering Footprint



DIMENSIONS: MILLIMETERS